| L Number | Hits | Search Text | DB | Time stamp |
|--------------|------|--|---|---------------------|
| - Number | 83 | laser same anneal\$3 same (silicon or si) and 117/904.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 15:58 |
| - | 12 | laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma and ion near3 beam | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 |
| | 78 | laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adjuapor adj deposition) same plasma same (si or silicon) | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 |
| _ | 41 | laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adjuapor adj deposition) same plasma same (si or silicon) and apparatus | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 |
| - | 15 | laser same (kev) same anneal\$3 and 117/\$4.ccls. | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 16:58 |
| - - | 5 | (CVD or chemical adj vapor adj deposition) same plasma and 117/98.ccls. | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 |
| - | | (CVD or chemical adj vapor adj deposition) same (si or silicon) and 117/98.ccls. | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 17:03 |
| - | 51 | (CVD or chemical adj vapor adj deposition) same plasma same ion same beam and 117/\$4.ccls. | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 17:04 |
| _ | 118 | ((CVD or chemical adj vapor adj deposition) same plasma) and 117/\$4.ccls. and ion near3 beam | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/05 17:09 |
| | 63 | ((CVD or chemical adj vapor adj deposition) same plasma) same (silicon or si) and 117/\$4.ccls. and ion near3 beam | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/06 |
| | | (CVD or chemical adj vapor adj deposition) same (silicon or si) and 117/\$4.ccls. and ion near3 beam same (ar or argon) | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/06 |
| <u> </u> | | | IBM_TDB | : |

| L Number | Hits | Search Text | DB | Time stamp |
|-------------|------|---|--|---------------------|
| | 76 | beam same (si or silicon) same (layer or film) same ion same amorphous and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; | 2002/09/09 |
| - | 12 | CVD near3 ion same (si or silicon) and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; | 2002/09/09 |
| : | | 11//\$4.6CIs. | US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 16:53 |
| - | 109 | CVD same plasma same ion and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/09 |
| - : | 68 | ion same (si or silicon) same (amorphous or seed or nucleus) same (beam or implant\$4) and 117/84-109.ccls. | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/10 |
| · - | 5 | ion same (si or silicon) same (amorphous or seed or nucleus) same (assist\$3) and 117/84-109.ccls. | IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 2002/09/10 13:27 |
| - | 17 | ion same (si or silicon) same ECR and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 2002/09/10 |
| - | 51 | (si or silicon) same (ECR or "electron cyclotron resonance") and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; | 2002/09/10 13:40 |
| - - | 19 | (si or silicon) same (ECR or "electron cyclotron resonance") same ion and 117/\$4.ccls. | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 2002/09/10 |
| · - | 82 | | DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 2002/09/10 15:16 |
| : - | 14 | ion same substrate same (beam) same (si or silicon) same (nucle\$4) and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 2002/09/10 15:50 |
| - | 41 | ion same substrate same (si or silicon) same (nucle\$4) and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; | 2002/09/10 16:08 |
| - ; | 127 | ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) and 117/\$4.ccls. | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 2002/09/10 16:54 |
| | 17 | ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) same ev and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/10 17:07 |
| | | | IBM_TDB | |

| · - | | | | |
|-----|---|---|--|--|
| | 9 | ion same (si or silicon) same amorphous same ev and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/10 17:10 |
| | _ | | : IBM_TDB | İ |
| _ | 6 | CVD same plasma same ev same (si or | USPAT; | 2002/09/10 |
| | | silicon) and 117/\$4.ccls. | US-PGPUB; | 17:16 |
| | | | EPO; JPO; | 1 |
| | | i | DERWENT; | |
| _ | 31 | CVD same plasma same (si or silicon) same | IBM_TDB USPAT; | 2002/00/10 |
| | - | energy and 117/\$4.ccls. | US-PGPUB; | 2002/09/10 17:12 |
| | | 1 | EPO; JPO; | 17.12 |
| | į | | DERWENT; | |
| | | | IBM TDB | |
| - | 4 | CVD same plasma same kev same (si or | USPAT; | 2002/09/10 |
| | | silicon) and 117/\$4.ccls. | US-PGPUB; | 17:16 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| _ | 72 | 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 | IBM_TDB | |
| | /3 | ion same (si or silicon) same amorphous same energy and 117/\$4.ccls. | USPAT; | 2002/09/11 |
| | | same energy and 117/54.ccis. | US-PGPUB; EPO; JPO; | 09:45 |
| | | • | DERWENT; | |
| | | | IBM TDB | İ |
| | . 83 | ion same (si or silicon) same amorphous | USPAT; | 2002/09/11 |
| | | same beam and 117/\$4.ccls. | US-PGPUB; | 10:08 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| _ | 81 | ion same (si or silicon) same | USPAT; | 2002/09/11 |
| | | polycrystal\$4 same beam and 117/\$4.ccls. | US-PGPUB; | 10:26 |
| | i | | EPO; JPO; | |
| | | | DERWENT; IBM TDB | |
| _ | 24 | ion same (si or silicon) same assist\$4 | USPAT; | 2002/09/11 |
| | | and 117/\$4.ccls. | US-PGPUB; | 10:44 |
| | ř | | EPO; JPO; | |
| | | : ! | DERWENT; | |
| | 1 | | IBM_TDB | |
| _ | 11 | plasma same cvd same ion same (kev or ev) | USPAT; | 2002/09/11 |
| | | and 117/\$4.ccls. | US-PGPUB; | 11:11 |
| | i | ! | EPO; JPO; | 1 |
| | | | DERWENT; | 1 |
| _ | 38 | ion near2 beam same (kev or ev) same (si | IBM_TDB USPAT; | 2002/09/12 |
| | | or silicon) and 117/\$4.ccls. | | 11:31 |
| | | | EPO; JPO; | . 11.51 |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 21 | ion near2 beam same (kev or ev) same | USPĀT; | 2002/09/12 |
| | | | US-PGPUB; | 13:23 |
| | | sputter\$3 and 117/\$4.ccls. | | |
| | | sputter\$3 and II//\$4.ccls. | EPO; JPO; | |
| | | sputter\$3 and II//\$4.ccls. | EPO; JPO; DERWENT; | |
| _ | 32 | | EPO; JPO; DERWENT; IBM_TDB | 2002/09/12 |
| _ | : 32 | ion near2 beam same mov\$4 and | EPO; JPO; DERWENT; IBM_TDB USPAT; | 2002/09/12 |
| _ | : 32 | | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; | 2002/09/12 13:37 |
| - | : 32 | ion near2 beam same mov\$4 and | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | |
| _ | : 32 | ion near2 beam same mov\$4 and | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; | |
| - | 1 · · · · · · · · · · · · · · · · · · · | ion near2 beam same mov\$4 and 117/\$4.ccls. ion same mov\$4 near4 substrate and | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | |
| _ | 1 · · · · · · · · · · · · · · · · · · · | ion near2 beam same mov\$4 and 117/\$4.ccls. | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; | 13:37 |
| - | 1 · · · · · · · · · · · · · · · · · · · | ion near2 beam same mov\$4 and 117/\$4.ccls. ion same mov\$4 near4 substrate and | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 13:37 |
| - | 1 . | ion near2 beam same mov\$4 and 117/\$4.ccls. ion same mov\$4 near4 substrate and | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 13:37 |
| - | 27 | ion near2 beam same mov\$4 and 117/\$4.ccls. ion same mov\$4 near4 substrate and 117/\$4.ccls. | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 13:37 2002/09/12 14:06 |
| - | 27 | ion near2 beam same mov\$4 and 117/\$4.ccls. ion same mov\$4 near4 substrate and 117/\$4.ccls. ion near3 beam same nucle\$5 and | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; | 13:37 2002/09/12 14:06 2002/09/12 |
| - | 27 | ion near2 beam same mov\$4 and 117/\$4.ccls. ion same mov\$4 near4 substrate and 117/\$4.ccls. | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; | 13:37 2002/09/12 14:06 |
| - | 27 | ion near2 beam same mov\$4 and 117/\$4.ccls. ion same mov\$4 near4 substrate and 117/\$4.ccls. ion near3 beam same nucle\$5 and | EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; | 13:37 2002/09/12 14:06 2002/09/12 |

| - | | 17 ion near3 beam same seed\$3 and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; | 2002709/12 16:45 |
|----|---|--|--|---------------------|
| •• | į | 17 ion near3 beam same clean\$3 and mbe and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; | 2002/09/12 17:06 |
| - | ! | ion near3 beam same (oxide or native) and mbe and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; | 2002/09/12 17:10 |
| ~ | ! | 138: ion same nucle\$4 and 117/\$4.ccls. | | 2002/09/13 09:22 |
| - | | ion same substrate same (si or silicon) same beam same \$3treat\$4 and 117/\$4.ccls. | DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2002/09/13 09:50 |
| | i | · | IBM_TDB | |